Band structure of new superconducting AlB$_2$-like ternary silicides M(Al$_{0.5}$Si$_{0.5}$)$_2$ and M(Ga$_{0.5}$Si$_{0.5}$)$_2$ (M= Ca, Sr and Ba).

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The electronic band structures of the new superconducting (with $T_C$ up to 7.7K) ternary silicides M(Al$_{0.5}$Si$_{0.5}$)$_2$ (M= Ca, Sr, Ba; A= Al, Ga) in the AlB$_2$-type structure have been investigated using the full-potential LMTO method. The calculations showed that the trend in transition temperatures doesn’t follow the changes in the density d-states at the Fermi level and probably is associated with phonon-mode frequencies.

The discovery of superconductivity (SC) in hexagonal AlB$_2$-like MgB$_2$ ($T_C \sim 39K$) and creation of promising materials based thereon$^{2-4}$ have attracted a great deal of interest in related compounds isostructural with magnesium diboride because of their potential as a new superconductors. One of the remarkable results is the synthesis of a floating zone and a Ar arc melting methods the series of the new ternary layered silicides Sr(Ga$_{0.5}$Si$_{0.5}$)$_2$, Ca(Al$_{0.5}$Si$_{0.5}$)$_2$ and (Ca,Sr,Ba)(Ga$_{0.5}$Si$_{0.5}$)$_2$ with transition temperatures ranging 3.3 - 7.7 K, except for Ba(Al$_{0.5}$Si$_{0.5}$)$_2$. They have the AlB$_2$-type structure in which Si and Al,Ga atoms are arranged in honeycomb sheets and alkaline-earth metals are intercalated between them. Furthermore, a series of the compounds (Ca,Sr,Ba)(Al$_{0.5}$Si$_{0.5}$)$_2$ were synthesized by varying Al/Si (0.6<x<1.2) and the maximum $T_C$ for these phases appears at the 1:1 composition.

Electrical resistivity and dc magnetization results$^{5-8}$ revealed that these layered silicides are a type-II superconductors. The observed different $T_C$ of these phases would be qualitatively attributed to the change in densities of states at $E_F$, $N(E_F)$ $^\dagger$. The Seebeck coefficient measurements for (Ca,Sr,Ba)(Al$_{0.5}$Si$_{0.5}$)$_2$ indicate that their carriers are predominantly electrons, in contrast to the holes in magnesium diboride$^{1-4}$.

Recently, the first band structure study of the layered silicides Sr(Ga$_{2}$Si$_{1-x}$)$_2$, x = 0.375, 0.5, 0.625 and Ca(Al$_{0.5}$Si$_{0.5}$)$_2$ has been performed$^{\ddagger}$. It has been shown that the SC properties may be due to the high density of (Ca,Sr)d-states at the Fermi level. In the present work we report the results of first-principles calculations for all known 1:1:1 ternary compounds M(Al$_{0.5}$Si$_{0.5}$)$_2$ (M=Ca, Sr, Ba; A=Al, Ga) and analyze the band structure parameters in association of SC properties for the isostructural and isoelectronic compounds: Ca(Al$_{0.5}$Si$_{0.5}$)$_2$, Sr(Al$_{0.5}$Si$_{0.5}$)$_2$, Ba(Al$_{0.5}$Si$_{0.5}$)$_2$ and Ca(Ga$_{0.5}$Si$_{0.5}$)$_2$, Sr(Ga$_{0.5}$Si$_{0.5}$)$_2$, Ba(Ga$_{0.5}$Si$_{0.5}$)$_2$. The band structures of the above silicides were calculated by the scalar relativistic full-potential LMTO method$^{\S}$. The lattice parameters used are listed in the Table 1.

Energy bands, total and site projected $\ell$-decomposed densities of states (DOS, LDOS) of M(Al$_{0.5}$Si$_{0.5}$)$_2$ are presented in Figs. 1-7. Let us discuss the band structures of M(Al$_{0.5}$Si$_{0.5}$)$_2$ for example Ca(Al$_{0.5}$Si$_{0.5}$)$_2$. The valence band (VB) for Ca(Al$_{0.5}$Si$_{0.5}$)$_2$ includes four fully occupied bands and has a width of about 10 eV. The quasi-core s-like band is located in the interval from 10.0 to 7.8 eV below the Fermi level and separated by a gap ($\sim$ 1.45 eV) from the hybrid (Al,Si)p-states which form four $\sigma$(2p$_{x,y}$) and two $\pi$(p$_z$) bands, Fig. 1. The E(k) dependence for p$_{x,y}$ and p$_z$ bands differs considerably. For 2p$_{x,y}$ bands the most pronounced dispersion of E(k) is observed along the direction k$_z$ (Γ-K of the Brillouin zone (BZ)). These bands are of the quasi two dimensional (2D) type. They form a quasi-flat zone along k$_z$ (Γ-A). The (Al,Si)p$_y$ orbitals participate strong covalent $\sigma$-states to form 2D honeycomb network bands of sp$^2$ type with the s states. The (Al,Si)p$_z$-like bands are responsible for weaker $\pi$(p$_z$) interactions. These 3D-type bands have the maximum dispersion in the direction k$_x$ (Γ-A). The Ca,p,d-states are admixed to p-like bands. The $\sigma$(p$_{x,y}$) and $\pi$(p$_z$) bands intersect at the Γ point of the BZ. It is important that the (Al,Si)p-bands are located below E$_F$ and do not contain hole states as well as those in non-superconducting AlB$_2$$^{2-4}$, which is isoelectronic to the Ca(Al$_{0.5}$Si$_{0.5}$)$_2$. The main contribution to the Ca(Al$_{0.5}$Si$_{0.5}$)$_2$ DOS in the vicinity of the Fermi level is made by the Ca3d-states: their contribution in N(E$_F$) is about 59 % compared with 9 % and 10% for Alp- and Sip-states, respectively. Let us compare the band structures of Ca(Al$_{0.5}$Si$_{0.5}$)$_2$, Sr(Al$_{0.5}$Si$_{0.5}$)$_2$ and Ba(Al$_{0.5}$Si$_{0.5}$)$_2$. The most obvious consequence of the alkaline-earth metal variation (Ca $\rightarrow$ Sr $\rightarrow$ Ba) is the decreasing of VB width from 10.0 (Ca(Al$_{0.5}$Si$_{0.5}$)$_2$) to $\sim$ 9.1 eV (Ba(Al$_{0.5}$Si$_{0.5}$)$_2$) caused by the increased cell volume. The location and dispersion of lowest d-bands depend from the alkaline-earth metals. As is seen from Fig.1, (Sr,Ba)d-states form the nearly flat bands in the direction L-H, close to E$_F$. As a result for Sr(Al$_{0.5}$Si$_{0.5}$)$_2$, Ba(Al$_{0.5}$Si$_{0.5}$)$_2$ the sharp peaks in LDOS of (Sr,Ba)d-states hybridized with (Al,Si)-orbitals, appear which are separated by a pseudogap from the bonding p-bands (Figs. 2-4).
values of N(E_F) increases more than twice going from Ca(Al_{0.5}Si_{0.5})_2 to Ba(Al_{0.5}Si_{0.5})_2. It is important to note that the increase in N(E_F) is due to simultaneously growth in LDOS of valence states for all atoms in silicides, see Table 1.

The band structures of M(Al_{0.5}Si_{0.5})_2 and M(Ga_{0.5}Si_{0.5})_2 are similar, Fig.1. Their differences are revealed in an increase in the dispersion of σ-, π-bands in the A-L-H directions an decrease in band gap (at ~1.0-0.9 eV) between s- and p-like bands for M(Ga_{0.5}Si_{0.5})_2 compared with M(Al_{0.5}Si_{0.5})_2. The VB width of M(Ga_{0.5}Si_{0.5})_2 increases by ~1.3-1.0 eV. The change of the alkaline-earth metal in the sequence Ca → Sr → Ba causes the increase of the N(E_F), the M d-states make the main contribution to near-Fermi DOS, Figs. 5-7, Table 1.

Thus, the band structure of the ternary AlB_2-like silicides is quite different from SC MgB_2. As compared by magnesium diboride, for M(Al_{0.5}Si_{0.5})_2 were found (i) the filling of the bonding p_{x,y}-bands and the absence of σ -holes, (ii) the increase of covalent interactions (due to p-d-hybridization) between graphene-like (Al, Si) or (Ga, Si) sheets and metal hexagonal layers and (iii) the principal change in the composition of N(E_F), where the alkaline-earth metal d-states make the main contributions (55-60 %, Table 1).

According to the experimental data^5−9: (i) in the silicides M(Al_{0.5}Si_{0.5})_2 the T_c decreases monotonically when the metal M is changed from Ca to Ba; (ii) in the silicides M(Ga_{0.5}Si_{0.5})_2 the T_c changes slightly (within range 3.9-5.1) with the maximum (5.1K) for Sr(Ga_{0.5}Si_{0.5})_2, Table 1.

In framework of BCS theory, the T_c can be estimated by the McMillan equation \( T_c \approx \frac{\omega}{\exp(\lambda)} \), where \( \omega > 0 \) is the averaged phonon frequency (inversely proportional to the atomic masses), \( \lambda \) is the electron-phonon coupling constant (\( \lambda = N(E_F) < I^2 > / M^2 < I^2 > \) is the electron-phonon matrix element, the value of \( < I^2 > \) does not depend on mass and is determined by force constants).

The values of N(E_F) (as the contributions in N(E_F) from Md-,(Si, Al, Ga)p-states) obtained here showed that (i) in the silicides M(Al_{0.5}Si_{0.5})_2 and M(Ga_{0.5}Si_{0.5})_2 N(E_F) increases monotonically when the alkaline-earth metal is changed from Ca to Ba (it is opposite to T_c trend^5−9), (ii) N(E_F) in the silicides M(Al_{0.5}Si_{0.5})_2 are higher than N(E_F) in the silicides M(Ga_{0.5}Si_{0.5})_2 based on the same M, what also does not correlate with the observed critical temperatures. Thus, the direct relationship T_c ∼ N(E_F), suggested in for the "strong stoichiometric" compositions of silicides M(Al_{0.5}Si_{0.5})_2 are impossible.

It may be supposed that the main factor, determining the variation in T_c in a number of isostructural and isostructural compounds M(Al_{0.5}Si_{0.5})_2, is the change of phonon frequencies depending from the atomic masses. Additionally, the shape of DOS (and the value of N(E_F)) may be changed owing to disorder in the distribution of (Al,Ge)/Si atoms in honeycomb layers. As a result alkaline-earth metals will be in different trigonal-prismatic positions, that may lead to the splitting of near-Fermi bands and to a decrease in N(E_F). This effect will be more strong for Sr, Ba-containing silicides, where for "ideal ordering" state the N(E_F) is determined by narrow intensive peaks in DOS, Figs. 3, 4, 6, 7. The possibility of chemical disordering and the inhomogeneity in the arc-melted samples of silicides were noted by authors of 1.

In summary, our calculations of the band structure of all known ternary silicides with the stoichiometry M(Al_{0.5}Si_{0.5})_2 showed that the Fermi level is located in the region of a sharp DOS peak originated mainly from alkaline-earth metal d-states with some contributions of (Al,Ge,Si)p-orbitals. The T_c behavior for the isostructural and isostructural M(Al_{0.5}Si_{0.5})_2 cannot be identified with the variation of N(E_F), and probably connected with phonon-mode frequencies determined by atomic masses.

Acknowledgement.

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TABLE I: The lattice parameters (a, Å, c/a [8]), total and site-projected $\ell$-decomposed DOSs at the Fermi level (N(E_F), states/eV) and transition temperatures (T_c, K) of silicides M(A_0.5Si_0.5)_2 (M=Ca, Sr, Ba; A=Al, Ga).

<table>
<thead>
<tr>
<th>Parameters</th>
<th>Ca(Al_{0.5}Si_{0.5})_2</th>
<th>Sr(Al_{0.5}Si_{0.5})_2</th>
<th>Ba(Al_{0.5}Si_{0.5})_2</th>
<th>Ca(Ga_{0.5}Si_{0.5})_2</th>
<th>Sr(Ga_{0.5}Si_{0.5})_2</th>
<th>Ba(Ga_{0.5}Si_{0.5})_2</th>
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<tr>
<td>c/a</td>
<td>1.0498</td>
<td>1.1171</td>
<td>1.1967</td>
<td>1.0777</td>
<td>1.1331</td>
<td>1.1985</td>
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<tr>
<td>M-s</td>
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<td>0.061</td>
<td>0.083</td>
<td>0.017</td>
<td>0.034</td>
<td>0.044</td>
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<td>0.073</td>
<td>0.036</td>
<td>0.076</td>
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<tr>
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<td>1.460</td>
<td>0.594</td>
<td>0.936</td>
<td>1.079</td>
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<tr>
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<td>0.0</td>
<td>0.0</td>
<td>0.108</td>
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<tr>
<td>Al(Ga)-s</td>
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<td>0.022</td>
<td>0.018</td>
<td>0.022</td>
<td>0.017</td>
<td>0.017</td>
</tr>
<tr>
<td>Al(Ga)-p</td>
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<td>Al(Ga)-d</td>
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<td>0.015</td>
<td>0.018</td>
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</tr>
<tr>
<td>Si-s</td>
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<td>0.019</td>
<td>0.014</td>
<td>0.013</td>
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<tr>
<td>Si-p</td>
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<td>0.241</td>
<td>0.237</td>
<td>0.105</td>
<td>0.163</td>
<td>0.164</td>
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<tr>
<td>Si-d</td>
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<td>0.066</td>
<td>0.042</td>
<td>0.051</td>
<td>0.051</td>
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<tr>
<td>Total</td>
<td>1.127</td>
<td>2.273</td>
<td>2.611</td>
<td>0.992</td>
<td>1.431</td>
<td>1.725</td>
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<td>T_c, K</td>
<td>7.8_7</td>
<td>4.5_7</td>
<td>&lt;2.8^9</td>
<td>4.3</td>
<td>5.1_8^9</td>
<td>3.9_8</td>
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FIG. 1: Energy bands: 1 - Ca(Al_{0.5}Si_{0.5})_2; 2 - Sr(Al_{0.5}Si_{0.5})_2; 3 - Ba(Al_{0.5}Si_{0.5})_2; 4 - Ca(Ga_{0.5}Si_{0.5})_2; 5 - Sr(Ga_{0.5}Si_{0.5})_2; 6 - Ba(Ga_{0.5}Si_{0.5})_2.
FIG. 2: Total and site-projected $\ell$-decomposed DOSs of Ca(Al$_{0.5}$Si$_{0.5}$)$_2$. The energies are relative to the Fermi level.

FIG. 3: Total and site-projected $\ell$-decomposed DOSs of Sr(Al$_{0.5}$Si$_{0.5}$)$_2$. The energies are relative to the Fermi level.
FIG. 4: Total and site-projected $\ell$-decomposed DOSs of Ba(Al$_{0.5}$Si$_{0.5}$)$_2$. The energies are relative to the Fermi level.

FIG. 5: Total and site-projected $\ell$-decomposed DOSs of Ca(Ga$_{0.5}$Si$_{0.5}$)$_2$. The energies are relative to the Fermi level.
FIG. 6: Total and site-projected $\ell$-decomposed DOSs of Sr(Ga$_{0.5}$Si$_{0.5}$)$_2$. The energies are relative to the Fermi level.

FIG. 7: Total and site-projected $\ell$-decomposed DOSs of Ba(Ga$_{0.5}$Si$_{0.5}$)$_2$. The energies are relative to the Fermi level.